



Attorney's Docket No.: 77-093002 / US3164D1.  
CUSTOMER NO. 26171

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hisashi Ohtani, et al.      Art Unit : 2815  
Serial No. : 09/379,702      Examiner : Eugene Lee  
Filed : August 24, 1999      Confirmation No.: 1613  
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICES

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**AMENDMENT**

In response to notice of appeal filed April 16, 2003, please amend the above-identified application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on page of this paper.

**Amendments to the Drawings** begin on page 7 of this paper and include both attached replacement sheets and annotated sheets showing changes.

**Remarks/Arguments** begin on page 8 of this paper.

An **Appendix** including amended drawing figures is attached following page 9 of this paper.

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In the drawings:

The attached sheets of drawings include changes to Figs. 1D, 2A, 2B, 2C and 2D. These sheets, which include Figs. 1A-2D, replace the original drawing sheets including Figs. 1A-2D.

The following changes have been made to the drawings:

Fig. 1D has been amended to replace erroneous reference numeral 108 with 104 so as to be consistent with Fig. 1E and the text.

Figs. 2A-2D have been amended to show that the gate insulating film 110 includes the first insulating film 104 and the second insulating film 109 as discussed at page 15, lines 18-22 of the application. Figs. 2A-2D also have been amended to move reference numeral 107 to a position in which the reference numeral does not interfere with the drawing.

**Attachments:** Replacement Sheets (2)  
Annotated Sheets Showing Changes (2)